

Haiqiang Jia

List of Publications by Year in descending order

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34
papers

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citations

840728

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23
g-index

36
all docs

36
docs citations

36
times ranked

843
citing authors

#	ARTICLE	IF	CITATIONS
1	Temperature-dependent photoluminescence in light-emitting diodes. Scientific Reports, 2014, 4, 6131.	3.3	122
2	Realization of high-luminous-efficiency InGaN light-emitting diodes in the "green gap" range. Scientific Reports, 2015, 5, 10883.	3.3	96
3	Investigation of temperature-dependent photoluminescence in multi-quantum wells. Scientific Reports, 2015, 5, 12718.	3.3	67
4	Enhancing the quantum efficiency of InGaN yellow-green light-emitting diodes by growth interruption. Applied Physics Letters, 2014, 105, .	3.3	41
5	The enhanced photo absorption and carrier transportation of InGaN/GaN Quantum Wells for photodiode detector applications. Scientific Reports, 2017, 7, 43357.	3.3	28
6	Indium segregation measured in InGaN quantum well layer. Scientific Reports, 2015, 4, 6734.	3.3	18
7	Improved optical and electrical performances of GaN-based light emitting diodes with nano truncated cone SiO ₂ passivation layer. Optical and Quantum Electronics, 2016, 48, 1.	3.3	17
8	Flexible ZnO Thin-Film Transistors on Thin Copper Substrate. IEEE Transactions on Electron Devices, 2018, 65, 3791-3795.	3.0	15
9	Visualizing carrier transitions between localization states in a InGaN yellow "green light-emitting-diode structure. Journal of Applied Physics, 2019, 126, .	2.5	14
10	Enhanced light extraction from AlGaInP-based red light-emitting diodes with photonic crystals. Optics Express, 2021, 29, 5993.	3.4	14
11	High performance visible-SWIR flexible photodetector based on large-area InGaAs/InP PIN structure. Scientific Reports, 2022, 12, 7681.	3.3	14
12	Characteristics of AlGaIn/GaN high electron mobility transistors on metallic substrate*. Chinese Physics B, 2020, 29, 048104.	1.4	10
13	Stripping GaN/InGaN epitaxial films and fabricating vertical GaN-based light-emitting diodes. Vacuum, 2021, 187, 110160.	3.5	10
14	Improvement of light power and efficiency droop in GaN-based LEDs using graded InGaN hole reservoir layer. Applied Physics A: Materials Science and Processing, 2014, 114, 1055-1059.	2.3	8
15	Improved crystal quality of non-polar a-plane GaN epi-layers directly grown on optimized hole-array patterned r-sapphire substrates. CrystEngComm, 2019, 21, 2747-2753.	2.6	8
16	Recent progress of GaN growth on maskless chemical-etched grooved sapphire substrate. Energy and Environmental Science, 2011, 4, 2625.	30.8	7
17	Characterization of periodicity fluctuations in InGaN/GaN MQWs by the kinematical simulation of X-ray diffraction. Applied Physics Express, 2019, 12, 045502.	2.4	7
18	Enhancement of light extraction efficiency of AlGaInP-based light emitting diodes by silicon oxide hemisphere array. Optics Communications, 2021, 481, 126539.	2.1	6

#	ARTICLE	IF	CITATIONS
19	Characterization of different-Al-content AlGaIn/GaN heterostructures on sapphire. Science China: Physics, Mechanics and Astronomy, 2010, 53, 49-53.	5.1	5
20	Effect of Stair-Case Electron Blocking Layer on the Performance of Blue InGaIn Based LEDs. Journal of Display Technology, 2014, 10, 146-150.	1.2	5
21	Luminescence study in InGaAs/AlGaAs multi-quantum-well light emitting diode with p-n junction engineering. Journal of Applied Physics, 2020, 127, 085706.	2.5	5
22	Improvement on InGaN-based light emitting diodes using GaN layer grown at low temperature in full N ₂ environment. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 1175-1178.	1.8	3
23	Effect of SU-8 Passivation Layer Induced Stress on the Performance of GaSb Diode. IEEE Photonics Technology Letters, 2018, 30, 1060-1063.	2.5	3
24	The impact of nanoporous SiN _x interlayer growth position on high-quality GaN epitaxial films. Science Bulletin, 2011, 56, 2739-2743.	1.7	2
25	Improvement in the crystal quality of non-polar a-plane GaN directly grown on an SiO ₂ stripe-patterned r-plane sapphire substrate. CrystEngComm, 2019, 21, 5124-5128.	2.6	2
26	The flexible LED fabrication by transferring epitaxial film onto PET. Optical Materials, 2021, 121, 111597.	3.6	2
27	N-polar GaN Film Epitaxy on Sapphire Substrate without Intentional Nitridation. Materials, 2022, 15, 3005.	2.9	2
28	Recent progress in single chip white light-emitting diodes with the InGaIn underlying layer. Science China: Physics, Mechanics and Astronomy, 2010, 53, 445-448.	5.1	1
29	The influence of pressure on the growth of a-plane GaN on r-plane sapphire substrates by MOCVD. Science China: Physics, Mechanics and Astronomy, 2011, 54, 446-449.	5.1	1
30	A novel method to reduce the period limitation in laser interference lithography. Optical and Quantum Electronics, 2015, 47, 2331-2338.	3.3	1
31	Influence of Sb ₂ soaking on strained InAs _{0.8} Sb _{0.2} /Al _{0.2} Ga _{0.8} Sb multiple quantum well interfaces. AIP Advances, 2021, 11, 075004.	1.3	1
32	Improving the Performance of Solar Cells Under Non-Perpendicular Incidence by Photonic Crystal. IEEE Photonics Journal, 2021, 13, 1-4.	2.0	1
33	Efficiency enhancement of InGaIn/GaN multiple quantum wells with graphene layer. Applied Physics A: Materials Science and Processing, 2015, 119, 1209-1213.	2.3	0
34	Monolithic light emitting device and light detecting device fabricated with a commercial LED wafer. Optical and Quantum Electronics, 2020, 52, 1.	3.3	0